NPN Silicon Planar Epitaxial Transistor

This NPN Silicon Epitaxial transistor is designed for use in linear and switching applications. The device is housed in the SOT-223 package which is designed for medium power surface mount applications.

Features

- PNP Complement is PZT2907AT1
- The SOT-223 Package Can be Soldered Using Wave or Reflow
- SOT-223 Package Ensures Level Mounting, Resulting in Improved Thermal Conduction, and Allows Visual Inspection of Soldered Joints
- The Formed Leads Absorb Thermal Stress During Soldering, Eliminating the Possibility of Damage to the Die
- Available in 12 mm Tape and Reel

MAXIMUM RATINGS

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant*

| Rating | Symbol | Value | Unit | | |
|---------------------------------------------------------------|--------------------|----------------------------|------|--|--|
| Collector-Emitter Voltage | V _{CEO} | 40 | Vdc | | |
| Collector-Base Voltage | V _{CBO} | 75 | Vdc | | |
| Emitter-Base Voltage (Open Collector) | V _{EBO} | 6.0 | Vdc | | |
| Collector Current | ۱ _C | 600 | mAdc | | |
| Total Power Dissipation up to $T_A = 25^{\circ}C$ (Note 1) | P _D 1.5 | | W | | |
| Storage Temperature Range | T _{stg} | _{tg} – 65 to +150 | | | |
| Junction Temperature | TJ | 150 | °C | | |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Device mounted on an epoxy printed circuit board 1.575 inches x 1.575 inches x 0.059 inches; mounting pad for the collector lead min. 0.93 inches².

THERMAL CHARACTERISTICS

| Rating | Symbol | Value | Unit |
|-----------------------------------------------------------------------------|----------------|-----------|-----------|
| Thermal Resistance, Junction-to-Ambient | R_{\thetaJA} | 83.3 | °C/W |
| Lead Temperature for Soldering, 0.0625" from case Time in Solder Bath | ΤL | 260 10 | °C Sec |

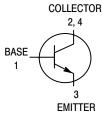


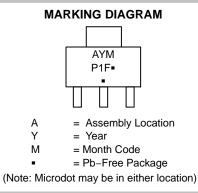
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http://onsemi.com

SOT-223 PACKAGE NPN SILICON TRANSISTOR SURFACE MOUNT







ORDERING INFORMATION

| Device | Package | Shipping [†] |
|--------------|----------------------|-----------------------|
| PZT2222AT1G | SOT-223 (Pb-Free) | 1,000 Tape & Reel |
| SPZT2222AT1G | SOT-223 (Pb-Free) | 1,000 Tape & Reel |
| PZT2222AT3G | SOT-223 (Pb-Free) | 4,000 Tape & Reel |

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

| Characteristic | Symbol | Min | Мах | Unit |
|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------|-----------------------------------------|----------------------------------------------|--------------|
| OFF CHARACTERISTICS | | | | |
| Collector–Emitter Breakdown Voltage ($I_C = 10 \text{ mAdc}, I_B = 0$) | V _{(BR)CEO} | 40 | _ | Vdc |
| Collector-Base Breakdown Voltage ($I_C = 10 \ \mu Adc$, $I_E = 0$) | V _{(BR)CBO} | 75 | - | Vdc |
| Emitter-Base Breakdown Voltage ($I_E = 10 \ \mu Adc, I_C = 0$) | age ($I_E = 10 \ \mu Adc, I_C = 0$) $V_{(BR)EBO}$ 6.0 | | - | Vdc |
| Base-Emitter Cutoff Current (V _{CE} = 60 Vdc, V _{BE} = - 3.0 Vdc) | I _{BEX} | - | 20 | nAdc |
| Collector-Emitter Cutoff Current (V_{CE} = 60 Vdc, V_{BE} = - 3.0 Vdc) | I _{CEX} | - | 10 | nAdc |
| Emitter–Base Cutoff Current ($V_{EB} = 3.0 \text{ Vdc}, I_C = 0$) | I _{EBO} | - | 100 | nAdc |
| Collector-Base Cutoff Current $(V_{CB} = 60 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 60 \text{ Vdc}, I_E = 0, T_A = 125^{\circ}\text{C})$ | Ісво | | 10 10 | nAdc μAdc |
| DN CHARACTERISTICS | I | | | |
| DC Current Gain ($I_C = 0.1 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$) ($I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$) ($I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$) ($I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$) ($I_C = 150 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$) ($I_C = 150 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 500 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$) ($I_C = 500 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$) | hFE | 35 50 70 35 100 50 40 | - - - 300 - - | _ |
| Collector-Emitter Saturation Voltages ($I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc}$) ($I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc}$) | V _{CE(sat)} | | 0.3 1.0 | Vdc |
| Base-Emitter Saturation Voltages ($I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc}$) ($I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc}$) | V _{BE(sat)} | 0.6 - | 1.2 2.0 | Vdc |
| Input Impedance ($V_{CE} = 10 \text{ Vdc}, I_C = 1.0 \text{ mAdc}, f = 1.0 \text{ kHz}$) ($V_{CE} = 10 \text{ Vdc}, I_C = 10 \text{ mAdc}, f = 1.0 \text{ kHz}$) | h _{ie} | 2.0 0.25 | 8.0 1.25 | kΩ |
| Voltage Feedback Ratio ($V_{CE} = 10 \text{ Vdc}, I_C = 1.0 \text{ mAdc}, f = 1.0 \text{ kHz}$) ($V_{CE} = 10 \text{ Vdc}, I_C = 10 \text{ mAdc}, f = 1.0 \text{ kHz}$) | h _{re} | - | 8.0x10 ⁻⁴ 4.0x10 ⁻⁴ | - |
| $ Small-Signal Current Gain \\ (V_{CE} = 10 Vdc, I_C = 1.0 mAdc, f = 1.0 kHz) \\ (V_{CE} = 10 Vdc, I_C = 10 mAdc, f = 1.0 kHz) $ | h _{fe} | 50 75 | 300 375 | - |
| Output Admittance ($V_{CE} = 10 \text{ Vdc}, I_C = 1.0 \text{ mAdc}, f = 1.0 \text{ kHz}$) ($V_{CE} = 10 \text{ Vdc}, I_C = 10 \text{ mAdc}, f = 1.0 \text{ kHz}$) | $V_{\rm CE} = 10 \rm Vdc, I_{\rm C} = 1.0 \rm mAdc, f = 1.0 \rm kHz)$ 5.0 | | 35 200 | μmhos |
| Noise Figure (V _{CE} = 10 Vdc, I _C = 100 μ Adc, f = 1.0 kHz) | F | - | 4.0 | dB |
| DYNAMIC CHARACTERISTICS | | | | |
| Current–Gain – Bandwidth Product ($I_C = 20 \text{ mAdc}, V_{CE} = 20 \text{ Vdc}, f = 100 \text{ MHz}$) | f _T | 300 | _ | MHz |
| Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz) | C _c | - | 8.0 | pF |
| Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz}$) | t Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz) C_e – 25 | | 25 | pF |
| SWITCHING TIMES $(T_A = 25^{\circ}C)$ | | | | |
| Delay Time $(V_{CC} = 30 \text{ Vdc}, I_C = 150 \text{ mAdc}, I_C = 150 \text$ | t _d | - | 10 | ns |
| Rise Time I _{B(on)} = 15 mAdc, V _{EB(off)} = 0.5 Vdc) Figure 1 | t _r | - | 25 | |
| Storage Time $(V_{CC} = 30 \text{ Vdc}, I_C = 150 \text{ mAdc},$ | t _s | _ | 225 | ns |
| Fall Time I _{B(on)} = I _{B(off)} = 15 mAdc) Figure 2 Figure 2 | t _f | _ | 60 | |

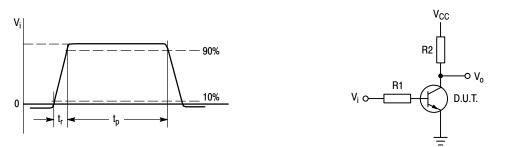


Figure 1. Input Waveform and Test Circuit for Determining Delay Time and Rise Time

| V _i = - 0.5 V to +9.9 V, | V_{CC} = +30 V, R1 = 619 Ω , R2 = 2 | 200 Ω. | |
|----------------------------------------------------------------|-------------------------------------------------------------------|--------------------------------------------------------------------|----------------------------------------------------------------------------|
| PULSE GENERATOR: PULSE DURATION RISE TIME DUTY FACTOR | $t_p 3 200 \text{ ns}$ $t_r 3 2 \text{ ns}$ $\delta = 0.02$ | OSCILLOSCOPE: INPUT IMPEDANCE INPUT CAPACITANCE RISE TIME | Z _i > 100 kΩ C _i < 12 pF t _r < 5 ns |

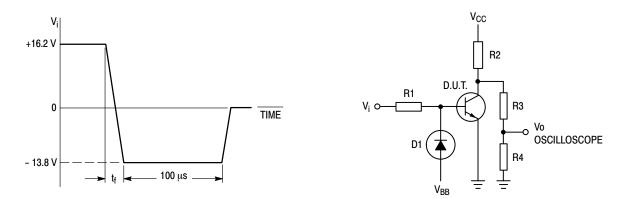
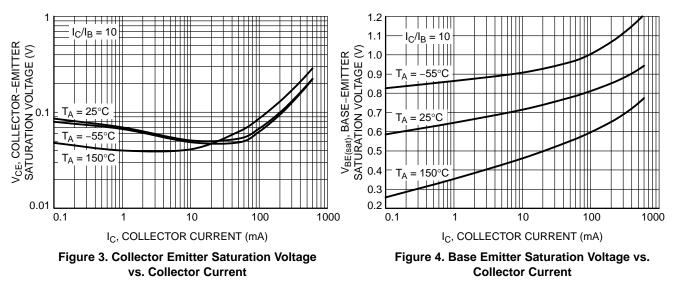
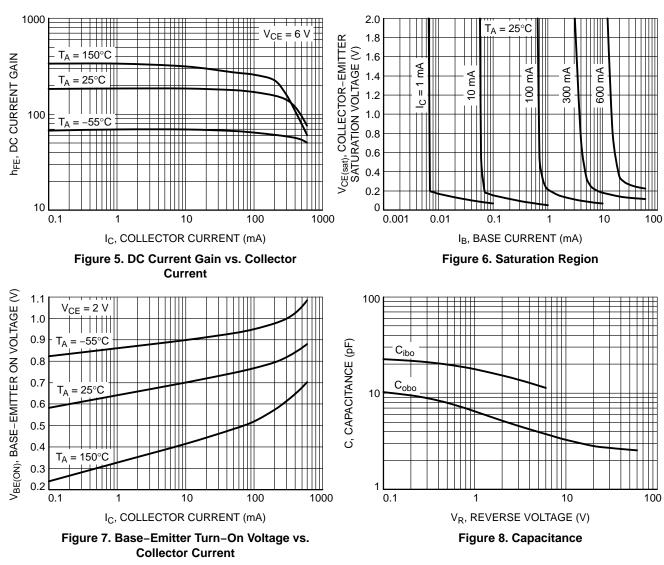


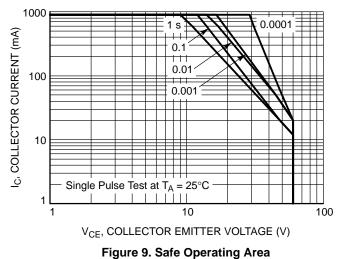
Figure 2. Input Waveform and Test Circuit for Determining Storage Time and Fall Time



TYPICAL CHARACTERISTICS



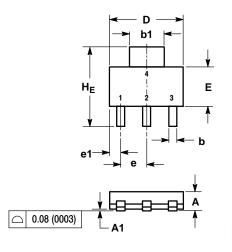
TYPICAL CHARACTERISTICS

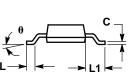


PACKAGE DIMENSIONS

SOT-223 (TO-261) CASE 318E-04

ISSUE N





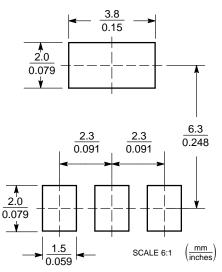
NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M.

| 199 | 14. | | | | | | |
|-----|---------------------------------|------|------|-------|--------|-------|--|
| 2. | 2. CONTROLLING DIMENSION: INCH. | | | | | | |
| | MILLIMETERS | | | | INCHES | | |
| DIM | MIN | NOM | MAX | MIN | NOM | MAX | |
| Α | 1.50 | 1.63 | 1.75 | 0.060 | 0.064 | 0.068 | |
| A1 | 0.02 | 0.06 | 0.10 | 0.001 | 0.002 | 0.004 | |
| b | 0.60 | 0.75 | 0.89 | 0.024 | 0.030 | 0.035 | |
| b1 | 2.90 | 3.06 | 3.20 | 0.115 | 0.121 | 0.126 | |
| С | 0.24 | 0.29 | 0.35 | 0.009 | 0.012 | 0.014 | |
| D | 6.30 | 6.50 | 6.70 | 0.249 | 0.256 | 0.263 | |
| Е | 3.30 | 3.50 | 3.70 | 0.130 | 0.138 | 0.145 | |
| е | 2.20 | 2.30 | 2.40 | 0.087 | 0.091 | 0.094 | |
| e1 | 0.85 | 0.94 | 1.05 | 0.033 | 0.037 | 0.041 | |
| L | 0.20 | | | 0.008 | | | |
| L1 | 1.50 | 1.75 | 2.00 | 0.060 | 0.069 | 0.078 | |
| HE | 6.70 | 7.00 | 7.30 | 0.264 | 0.276 | 0.287 | |
| θ | 0° | - | 10° | 0° | - | 10° | |

PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR

STYLE 1:

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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